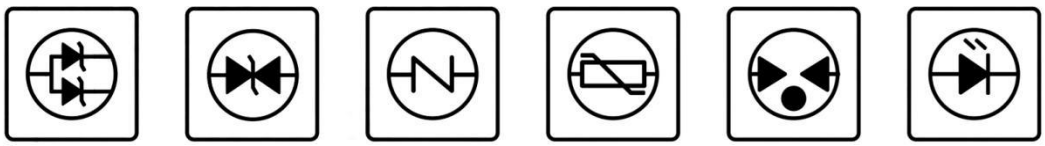
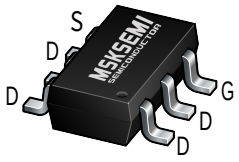
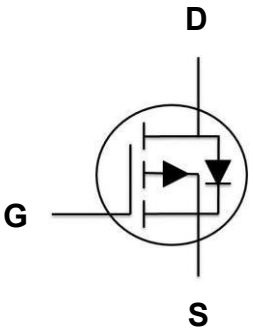
MSKSEMI
SEMICONDUCTOR



Product data sheet



SOT-23-6



Features

- *-20V,-4.5A, RDS(ON) =40mΩ@VGS = -4.5V*
- *Improved dv/dt capability*
- *Fast switching*
- *Green Device Available*

Applications

- *Notebook*
- *Load Switch*
- *Networking*

BVDSS	RDSON	ID
-20V	40mΩ	-4.5A

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Drain Current – Continuous (T_A=25℃)	-4.5	A
	Drain Current – Continuous (T_A=70℃)	-3.2	A
I_{DM}	Drain Current – Pulsed[1]	-18	A
P_D	Power Dissipation (T_A=25℃)	1.56	W
	Power Dissipation – Derate above 25℃	0.012	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-20	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-20V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-16V , V_{GS}=0V , T_J=125℃	---	---	-10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±12V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-4.5V , I_D=-3A	---	40	50	mΩ
		V_{GS}=-2.5V , I_D=-2A	---	50	70	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-0.5	-0.65	-1.1	V
gfs	Forward Transconductance	V_{DS}=-10V , I_S=-3A	---	6	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=-10V , V_{GS}=-4.5V , I_D=-2A	---	6.4	---	nC
Q_{gs}	Gate-Source Charge[2,3]		---	0.9	---	
Q_{gd}	Gate-Drain Charge[2,3]		---	1.6	---	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DD}=-10V , V_{GS}=-4.5V , R_G=6Ω I_D=-2A	---	5	---	nS
T_r	Rise Time[2,3]		---	17.4	---	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	40.7	---	
T_f	Fall Time[2,3]		---	11.4	---	
C_{iss}	Input Capacitance	V_{DS}=-10V , V_{GS}=0V , F=1MHz	---	540	---	pF
C_{oss}	Output Capacitance		---	80	---	
C_{rss}	Reverse Transfer Capacitance		---	75	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	-4.5	A
I_{SM}	Pulsed Source Current		---	---	-9.0	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

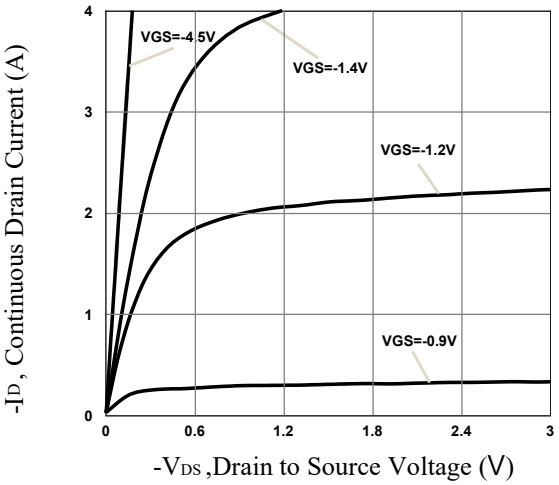


Fig.1 Typical Output Characteristics

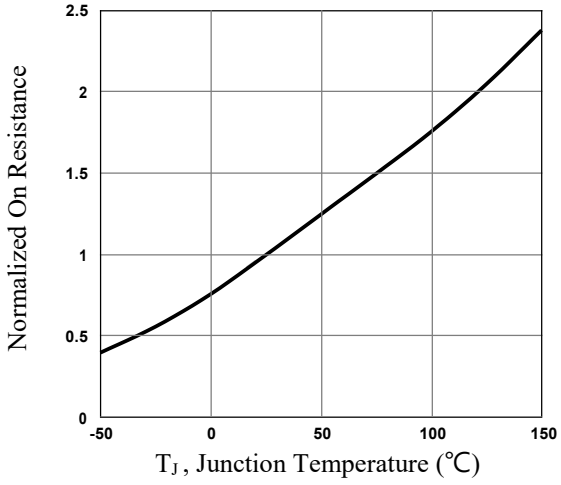


Fig.2 Normalized RDSON vs. T_J

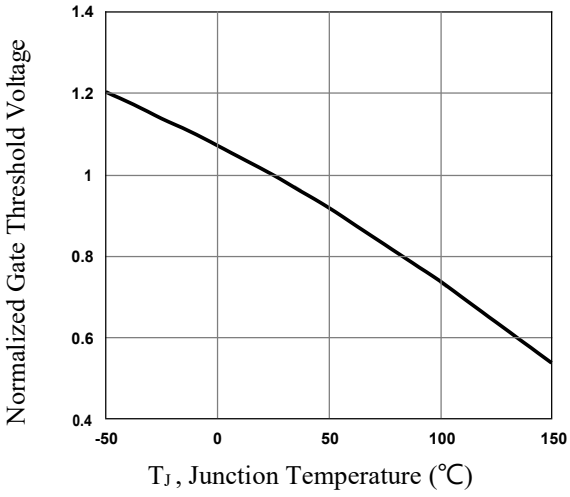


Fig.3 Normalized V_{th} vs. T_J

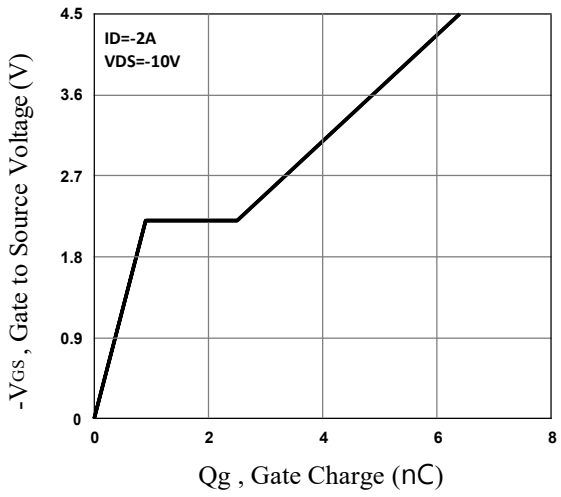


Fig.4 Gate Charge Waveform

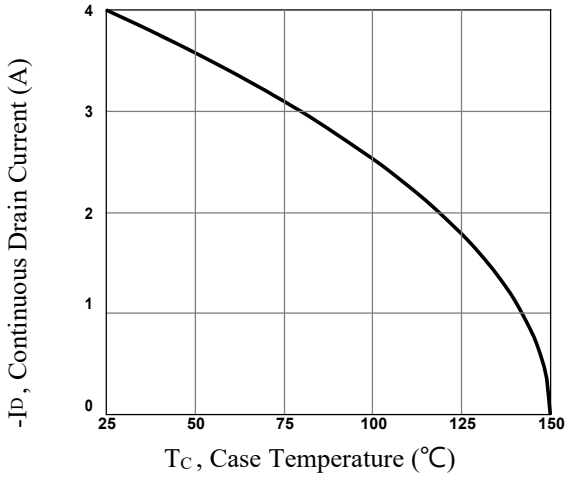


Fig.5 Continuous Drain Current vs. T_C

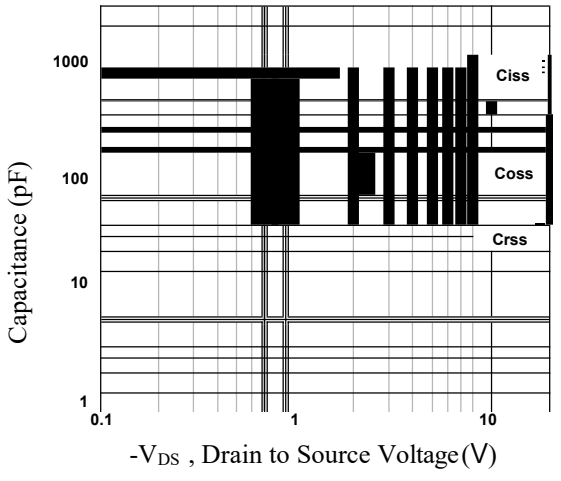
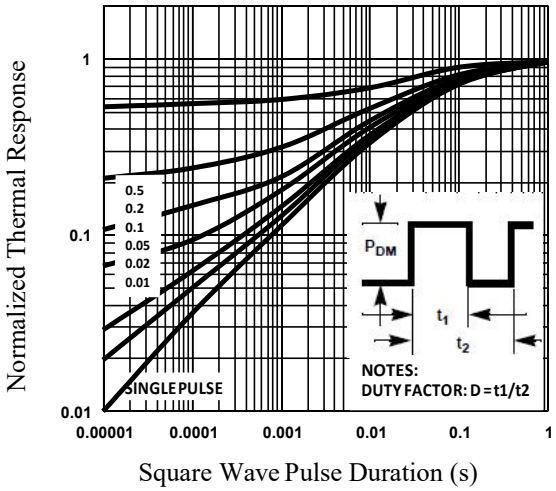


Fig.6 Capacitance Characteristics



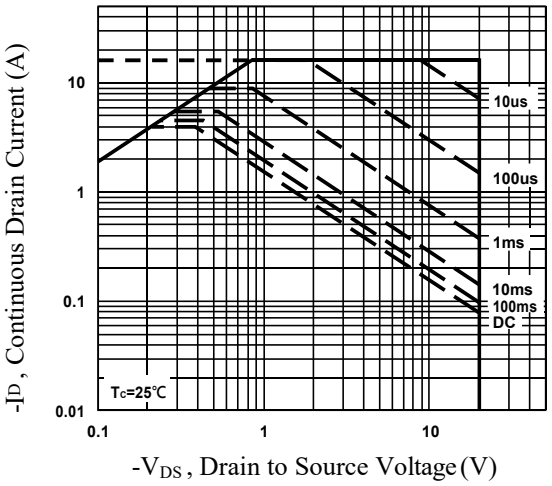
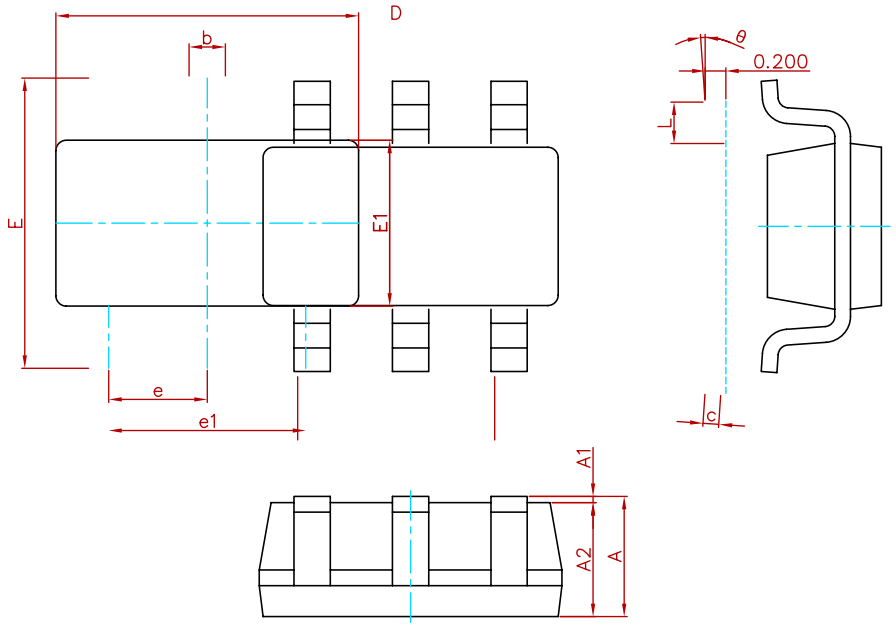


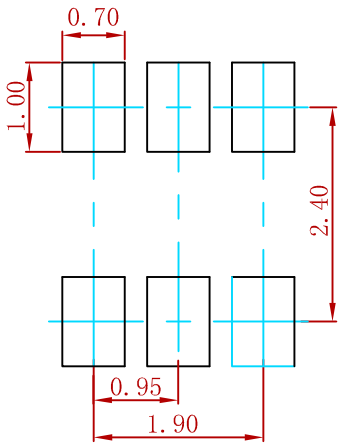
Fig.7 Normalized Transient Impedance

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
FDC606P-MS	SOT-23-6	3000

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